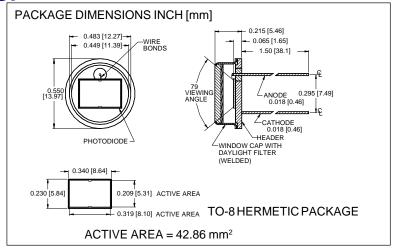
PHOTONIC Silicon Photodiode, Blue Enhanced Photoconductive with daylight filter Type PDB-C109F





FEATURES

- High speed
- Low capacitance
- Blue enhanced
- Low dark current

DESCRIPTION

The **PDB-C109F** is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a hermetic TO-8 metal can with a flat window and a daylight filter.

APPLICATIONS

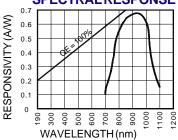
- Instrumentation
- Industrial controls
- Laser detection
- Power meter sensors

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
V _{BR}	Reverse Voltage		100	V	
T _{STG}	Storage Temperature	-55	+150	∘C	
To	Operating Temperature Range	-40	+125	∘C	
Ts	Soldering Temperature*		+240	∘C	
IL	Light Current		0.5	mA	

 $^{^{\}star}$ 1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	450	500		m A
ΙD	Dark Current	H = 0, V _R = 10 V		5	15	nA
Rsh	Shunt Resistance	H = 0, V _R = 10 mV	30	100		МΩ
TC Rsh	Rsн Temp. Coefficient	H = 0, V _R = 10 mV		-8		%/℃
Cı	Junction Capacitance	H = 0, V _R = 10 V**		120		pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		950		nm
VBR	Breakdown Voltage	I = 10 m A	30	50		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		5x10 ⁻¹³		W/ √Hz
tr	Response Time	RL = 1 KΩ V _R = 50 V		25		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1 MHz